

V_{WM} = 5V, 2pF ESD Protection Diode

FEATURES

Meet IEC61000-4-2(ESD) ±15kV(air), ±8kV(contact)

Working Voltage: 5V

• Moisture sensitivity level: level 1, per J-STD-020

RoHS Compliant

• Halogen-free according to IEC 61249-2-21

APPLICATIONS

• High Speed Data Lines: USB 2.0 / VGA/ DVI /SDI

• Notebooks, Desktops and Servers

Touch Panel

MECHANICAL DATA

• Case: DFN1006L

• Molding compound meets UL 94V-0 flammability rating

• Terminal: Matte tin plated leads, solderable per J-STD-002

Meet JESD 201 class 1A whisker test

• Polarity: As marked

• Weight: 0.742mg (approximately)

KEY PARAMETERS			
PARAMETER	VALUE	UNIT	
P _{PPSM}	100	W	
I_{PP}	3	Α	
V_{WM}	5	V	
V_{BR} at $I_R = 1 \text{ mA}$	6	V	
V_C at $I_{PP} = 3$ A	15	V	
Package	DFN1006L		
Configuration	Single die		









DFN1006L



PARAMETER	SYMBOL	TESD5V0L1UC	UNIT
Marking code on the device		BH	
Rated random recurring peak Impulse power dissipation (tp = 8/20µs waveform)	P _{PPSM}	100	W
Peak impulse current (tp = 8/20µs waveform)	I _{PP}	3	А
ESD per IEC 61000-4-2 (Air)		±15	kV
ESD per IEC 61000-4-2 (Contact)	V _{ESD}	±8	kV
Junction temperature range	T _J	-55 to +150	°C
Storage temperature range	T _{STG}	-55 to +150	°C



TESD5V0L1UC Taiwan Semiconductor

ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Reverse breakdown voltage ⁽¹⁾	I _R = 1 mA	V_{BR}	6	-	9.8	V
Rated working standoff voltage		V _{WM}	-	-	5	V
Reverse current ⁽¹⁾	V _R = 5 V	I _R	-	-	0.1	μA
Clamping voltage ⁽²⁾	I _{PP} = 1 A	V	-	-	10	V
Clamping voltage ⁽²⁾	I _{PP} = 3 A	- V _C	-	-	15	V
Junction capacitance	$f = 1MHz, V_R = 0V$	CJ	-	-	2	pF

Notes:

- 1. Pulse test with PW = 30ms
- 2. $tp = 8/20\mu s$ waveform

ORDERING INFORMATION			
ORDERING CODE	PACKAGE	PACKING	
TESD5V0L1UC RJG	DFN1006L	10K / 7" Reel	



CHARACTERISTICS CURVES

(T_A = 25°C unless otherwise noted)

Fig.1 8/20µs pulse waveform

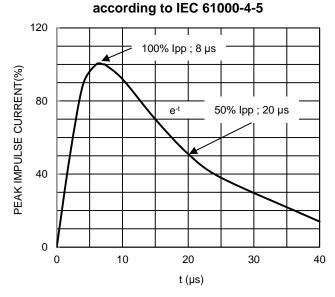


Fig.2 ESD pulse waveform according to IEC 61000-4-2

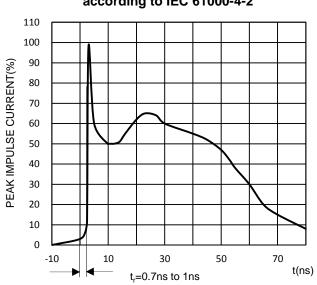


Fig.3 TLP I-V Curve

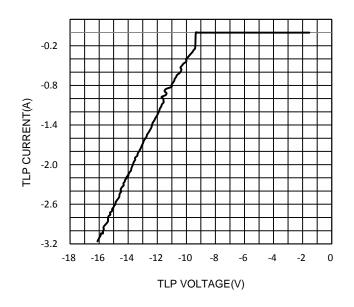
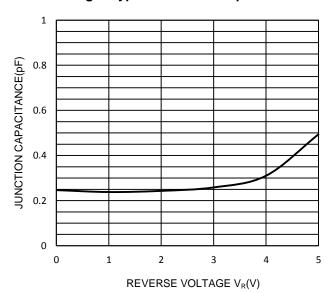


Fig.4 Typical Junction Capacitance

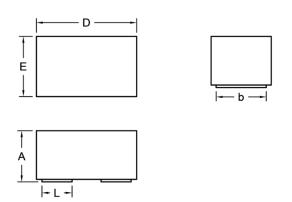






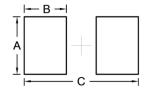
PACKAGE OUTLINE DIMENSION

DFN1006L



DIM.	Unit (mm)		Unit (inch)	
Dilvi.	Min.	Max.	Min.	Max.
Α	0.46	0.51	0.018	0.020
b	0.50	(TYP.)	0.020	(TYP.)
D	0.95	1.05	0.037	0.041
E	0.55	0.65	0.022	0.026
L	0.30	(TYP.)	0.012	(TYP.)

SUGGESTED PAD LAYOUT



Symbol	Unit (mm)	Unit (inch)
Α	0.56	0.022
В	0.41	0.016
С	1.11	0.044



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